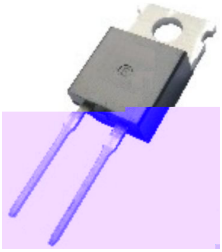
TO-220AC
Ultrafast Recovery Diode in a TO-220AC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 2 Cathode PIN 3 Anode

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Forward Current	I_F	1 15	A
Peak forward surge current	I_{FSM}	200	A
Typical Thermal Resistance Junction to Case	R_{Jc}	1.5	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

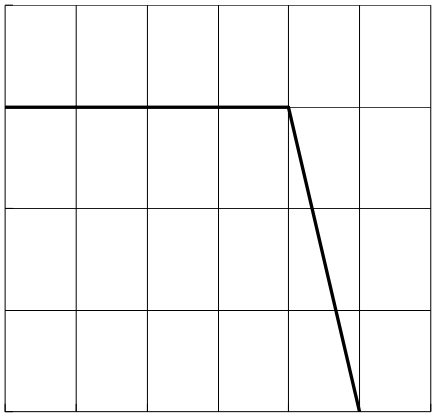
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R=1mA	200			V
Forward Voltage	V_F	I_F=3.0A T_C=25		0.76	0.85	V
		I_F=3.0A T_C=150		0.55	0.65	
		I_F=15A T_C=25			1.05	
		I_F=15A T_C=150			0.85	
Instantaneous Reverse Current(Note1)	I_R	V_R=200V T_a=25			10	A
		V_R=140V T_a=150			100	
		V_R=200V T_a=150			500	
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A, I_{RR}=0.25A			35	ns

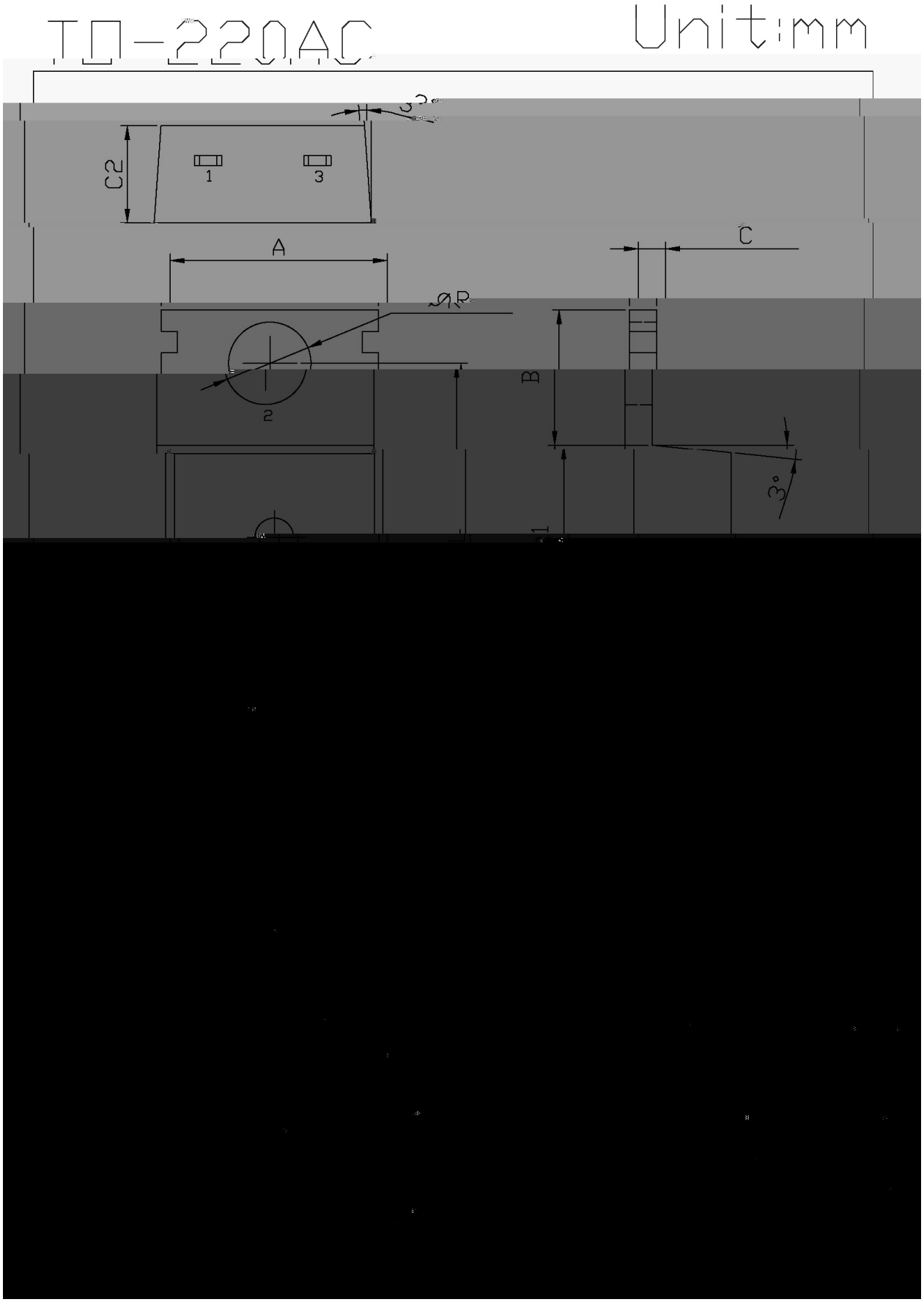
/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

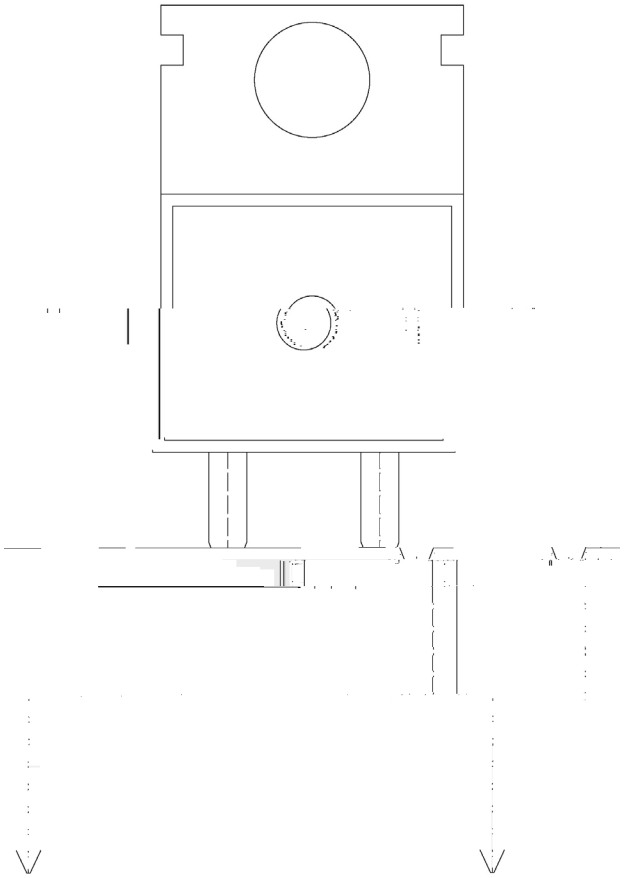
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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MUR1520

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Note:

BR:	Company Code
MUR1520	Product Type.